Power MOSFET

20 V, 890 mA, Single N-Channel with ESD Protection, SOT-723

Features

- N-Channel Switch with Low R_{DS(on)}
- 44% Smaller Footprint and 38% Thinner than SC89
- Low Threshold Levels Allowing 1.5 V R_{DS(on)} Rating
- Operated at Low Logic Level Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switching
- Interface Switching
- Logic Level Shift
- Battery Management for Ultra Small Portable Electronics

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	20	V	
Gate-to-Source Volt	age		V_{GS}	±8	V
Continuous Drain	Steady T _A = 25°C		I _D	890	mA
Current (Note 1)	State	T _A = 85°C		640	
	t ≤ 5 s	T _A = 25°C		990	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	450	mW
	t ≤ 5 s			550	
Continuous Drain	Steady State	T _A = 25°C	I _D	750	mA
Current (Note 2)	State	T _A = 85°C		540	
Power Dissipation (Note 2)		T _A = 25°C	P _D	310	mW
Pulsed Drain Current	t _p = 10 μs		I _{DM}	1.8	Α
Operating Junction and Storage Temperature		T _J , T _{STG}	–55 to 150	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
- 2. Surface mounted on FR4 board using the minimum recommended pad size

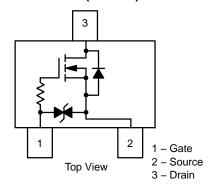


ON Semiconductor®

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V _{(BR)DSS}	R _{DS(on)} TYP	I _D Max	
20 V	0.20 Ω @ 4.5 V	890 mA	
	0.26 Ω @ 2.5 V	790 mA	
	0.43 Ω @ 1.8 V	700 mA	
	0.56 Ω @ 1.5 V	200 mA	

SOT-723 (3-LEAD)





SOT-723 CASE 631AA STYLE 5

MARKING DIAGRAM



KF = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTK3134NT1G	SOT-723	4000 / Tape & Reel
NTK3134NT5G	SOT-723	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ hetaJA}$	280	°C/W
Junction-to-Ambient - t = 5 s (Note 3)	$R_{ heta JA}$	228	
Junction-to-Ambient - Steady State Minimum Pad (Note 4)	$R_{ heta JA}$	400	

^{3.} Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
4. Surface mounted on FR4 board using the minimum recommended pad size

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μA		20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 250 μA, Reference	I _D = 250 μA, Reference to 25°C		18		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V,	T _J = 25°C			1.0	μΑ
		$V_{DS} = 16 \text{ V}$	T _J = 125°C			2.0	
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm$	4.5 V			±0.5	μΑ
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = 25$	50 μΑ	0.45		1.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				2.4		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 89$	90 mA		0.20	0.35	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 78$	80 mA		0.26	0.45	
		V _{GS} = 1.8 V, I _D = 70	00 mA		0.43	0.65	
		V _{GS} = 1.5 V, I _D = 200 mA			0.56	1.2	
Forward Transconductance	9 _{FS}	V _{DS} = 10 V, I _D = 800 mA			1.6		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}, V_{DS} = 16 \text{ V}$			79	120	pF
Output Capacitance	C _{OSS}				13	20	
Reverse Transfer Capacitance	C _{RSS}				9.0	15	
SWITCHING CHARACTERISTICS, V	/ _{GS} = 4.5 V (Note	e 6)					
Turn On Delay Time	t _{d(ON)}	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V}, I$	_D = 500 mA,		6.7		ns
Rise Time	t _r	$R_G = 10 \Omega$			4.8		
TurnOff Delay Time	t _{d(OFF)}				17.3		
Fall Time	t _f				7.4		
DRAIN SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 350 \text{ mA}$	T _J = 25°C		0.75	1.2	V
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V}, d_{ISD}/d_t = 100 \text{ A/}\mu\text{s},$ $I_S = 1.0 \text{ A}, V_{DD} = 20 \text{ V}$			8.1		ns
Charge Time	ta				6.4		
Discharge Time	t _b				1.7		
Reverse Recovery Charge	Q_{RR}				3.0		nC
-							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{5.} Pulse Test: pulse width = $300 \mu s$, duty cycle = 2%

^{6.} Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

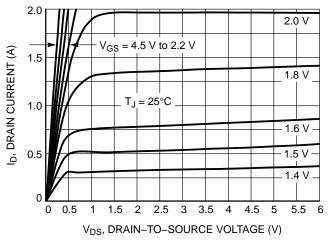


Figure 1. On-Region Characteristics

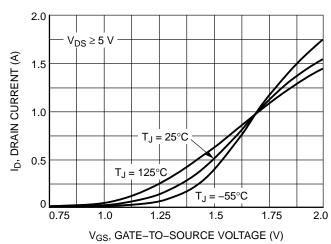


Figure 2. Transfer Characteristics

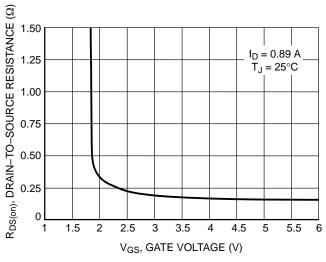


Figure 3. On-Resistance vs. Gate-to-Source Voltage

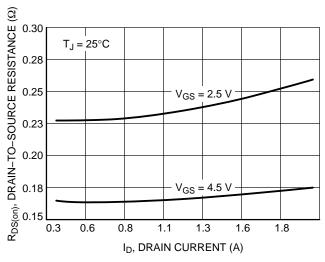


Figure 4. On–Resistance vs. Drain Current and Gate Voltage

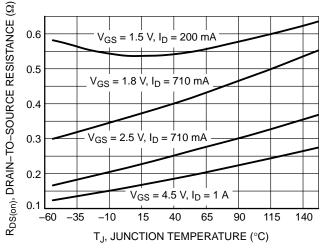


Figure 5. On–Resistance Variation with Temperature

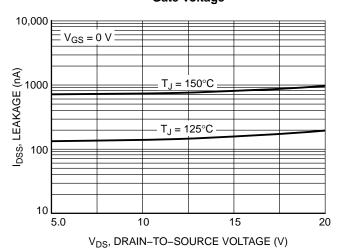


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

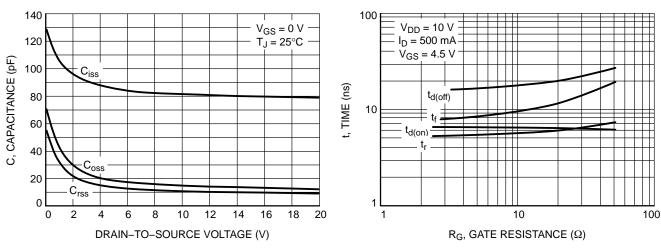


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

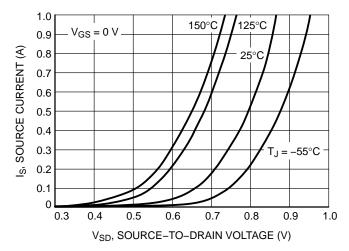
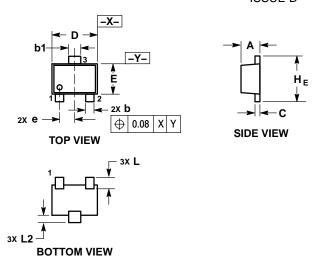


Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SOT-723 CASE 631AA ISSUE D

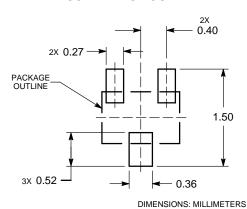


- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- T 14.3M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD
 FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.45	0.50	0.55		
b	0.15	0.21	0.27		
b1	0.25	0.31	0.37		
С	0.07	0.12	0.17		
D	1.15	1.20	1.25		
Ε	0.75	0.80	0.85		
е	0.40 BSC				
ΗE	1.15	1.20	1.25		
L	0.29 REF				
12	0.15	0.20	0.25		

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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